

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	400 650	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	800	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 150$	P_{tot}	2250	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

				min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$		1,70 2,00	2,15	V V
栅极阈值电压 Gate threshold voltage	$I_C = 16,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,0	5,8	6,5	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G		3,70		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}		1,9		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}		28,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}		1,10		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,8\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_{don}		0,25 0,30		μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,8\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_r		0,09 0,10		μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,8\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_{doff}		0,55 0,65		μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,8\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_f		0,13 0,18		μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}, L_S = 85\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,8\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{on}		33,0		mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}, L_S = 85\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,8\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{off}		59,0		mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\text{ }\mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		I_{SC}		1600		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}			0,055	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40		125	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	400	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1 \text{ ms}$	I_{FRM}	800	A
I_{2t} -值 I_{2t} - value	$V_R = 0 \text{ V}$, $t_P = 10 \text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	I_{2t}	31000	A ² s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 400 \text{ A}$, $V_{GE} = 0 \text{ V}$ $I_F = 400 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	V_F	1,65 1,65	2,15	V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 400 \text{ A}$, $-di_F/dt = 4000 \text{ A}/\mu\text{s}$ ($T_{vj}=125^{\circ}\text{C}$) $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	I_{RM}	280 360		A A
恢复电荷 Recovered charge	$I_F = 400 \text{ A}$, $-di_F/dt = 4000 \text{ A}/\mu\text{s}$ ($T_{vj}=125^{\circ}\text{C}$) $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	Q_r	40,0 75,0		μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 400 \text{ A}$, $-di_F/dt = 4000 \text{ A}/\mu\text{s}$ ($T_{vj}=125^{\circ}\text{C}$) $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{rec}	18,0 34,0		mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,125	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj \text{ op}}$	-40	125	$^{\circ}\text{C}$

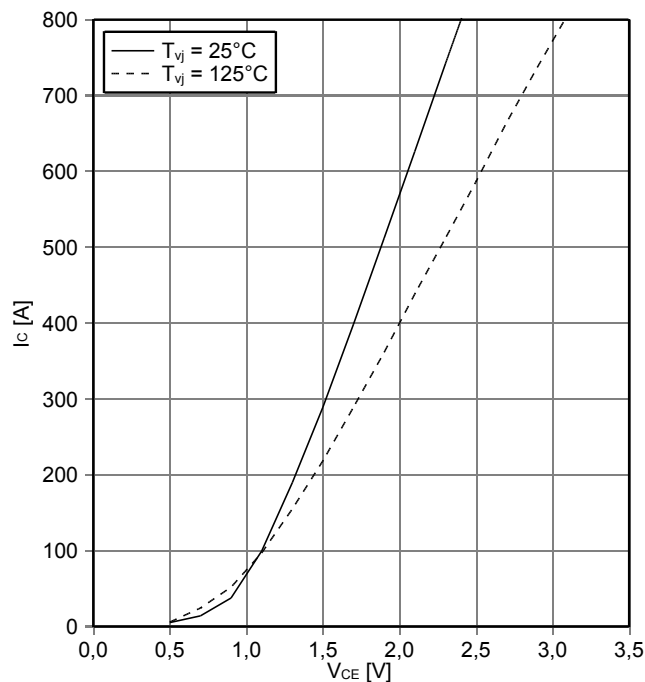
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃	
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		20,0	mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		11,0	mm
相对电痕指数 Comperative tracking index		CTI	> 425	
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个模块 / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}	min. 0,01	typ. max. K/W
杂散电感,模块 Stray inductance module		L _{sCE}	16	nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T _C = 25°C, 每个开关 / per switch	R _{CC'+EE'}	0,50	mΩ
储存温度 Storage temperature		T _{stg}	-40	125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00	- 6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	1,1	- 2,0 Nm
			2,5	- 5,0 Nm
重量 Weight		G	340	g

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

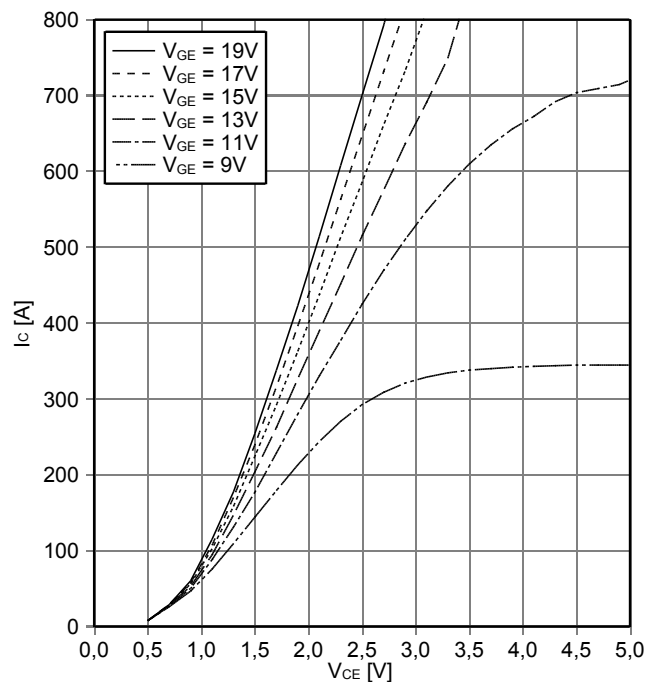
$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

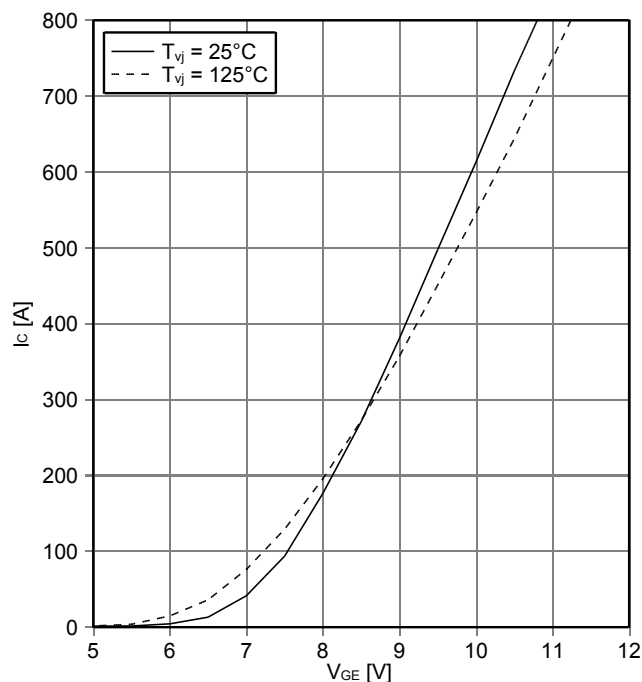
$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

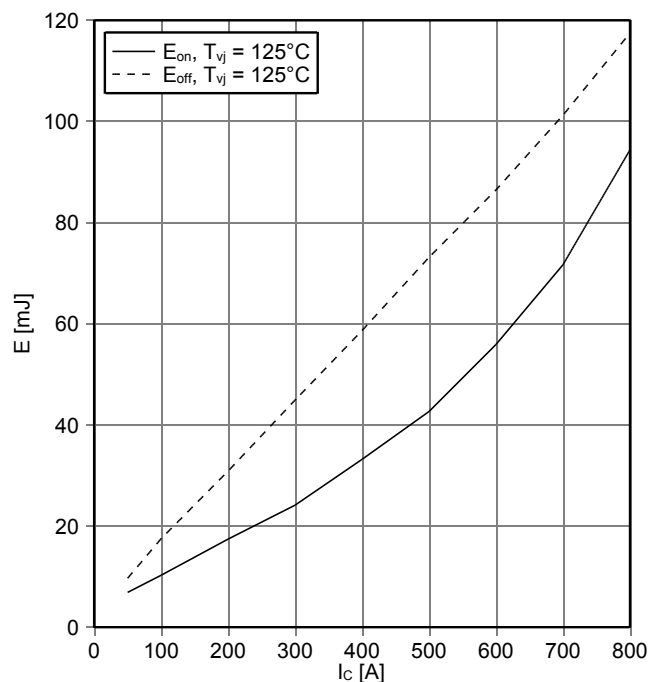
$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

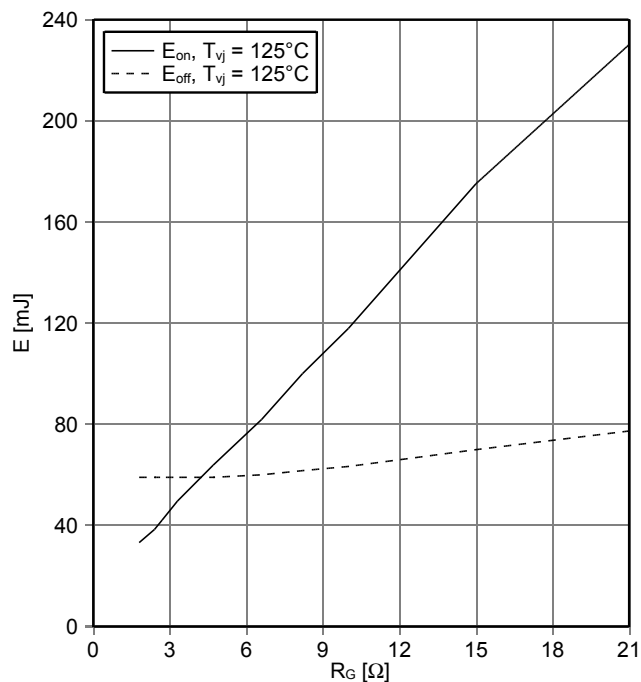
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1.8\ \Omega$, $R_{Goff} = 1.8\ \Omega$, $V_{CE} = 600\text{ V}$



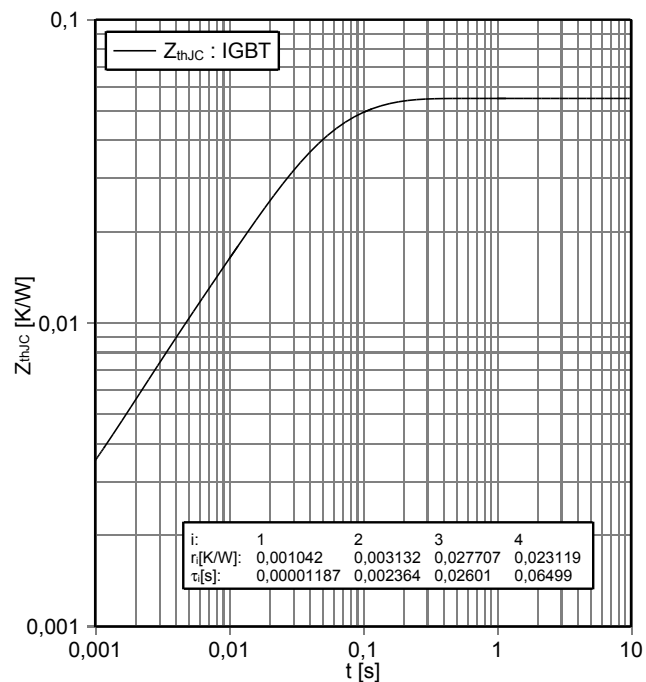
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 400\text{ A}$, $V_{CE} = 600\text{ V}$



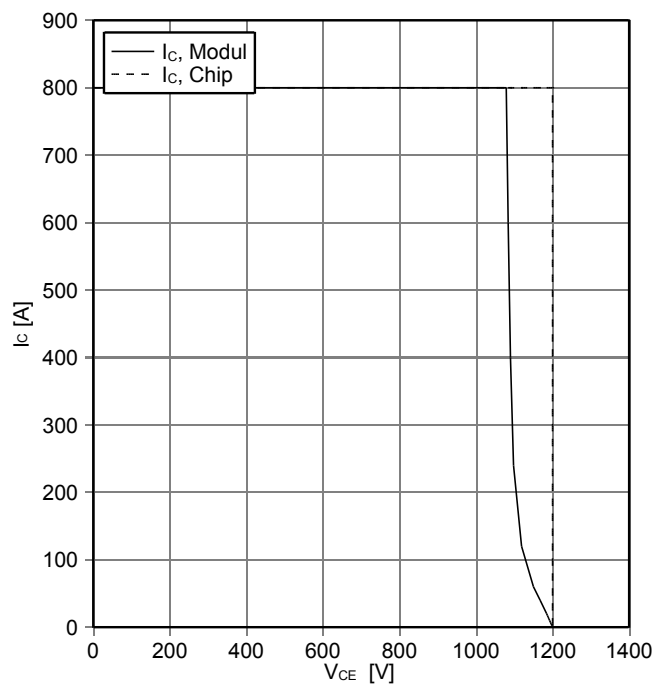
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



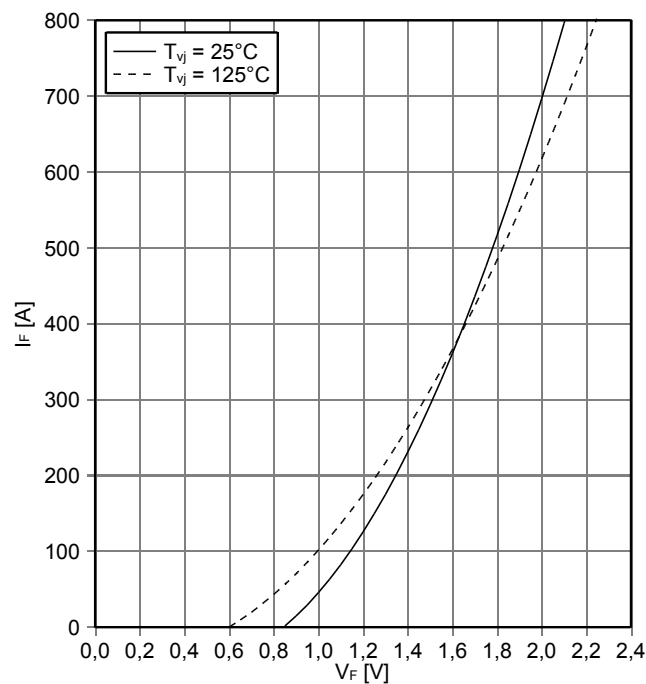
反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1.8\text{ Ω}$, $T_{vj} = 125^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



prepared by: MM

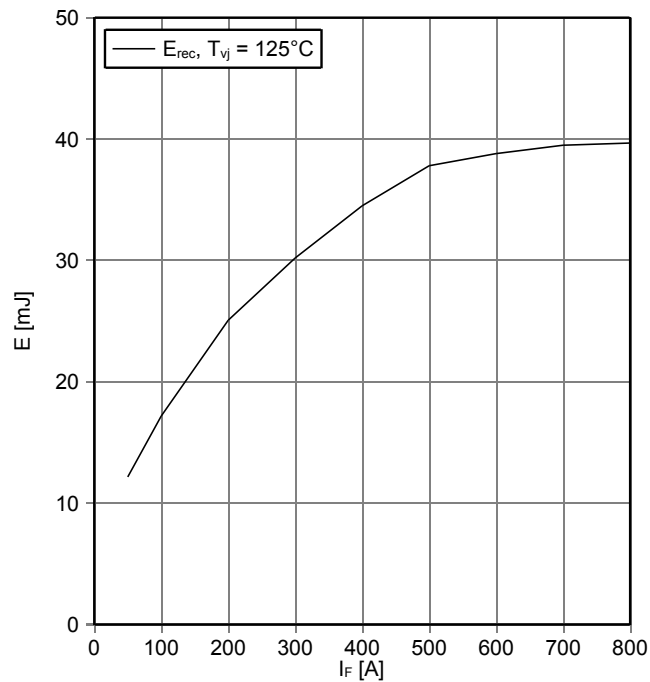
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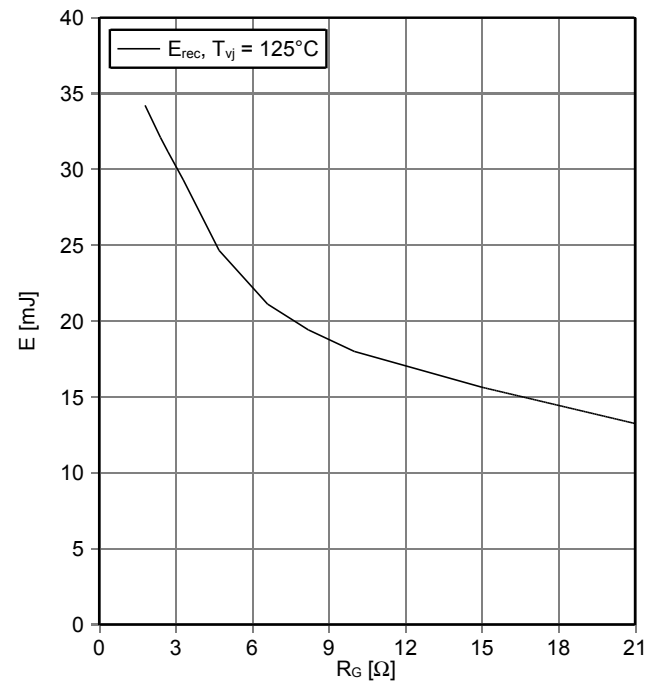
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1.8 \Omega$, $V_{CE} = 600 V$

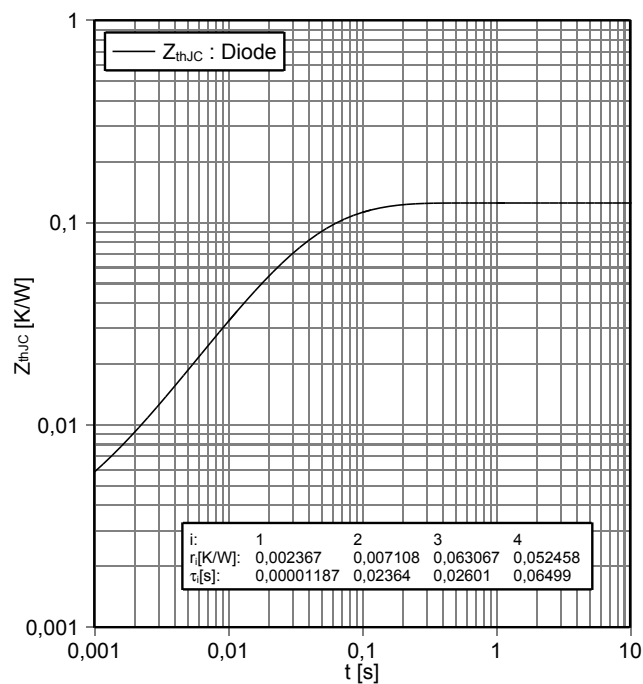


开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 400 A$, $V_{CE} = 600 V$



瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
 $Z_{thJC} = f(t)$

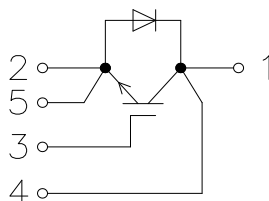


i:	1	2	3	4
r_i [K/W]:	0.002367	0.007108	0.063067	0.052458
τ_i [s]:	0.00001187	0.02364	0.02601	0.06499

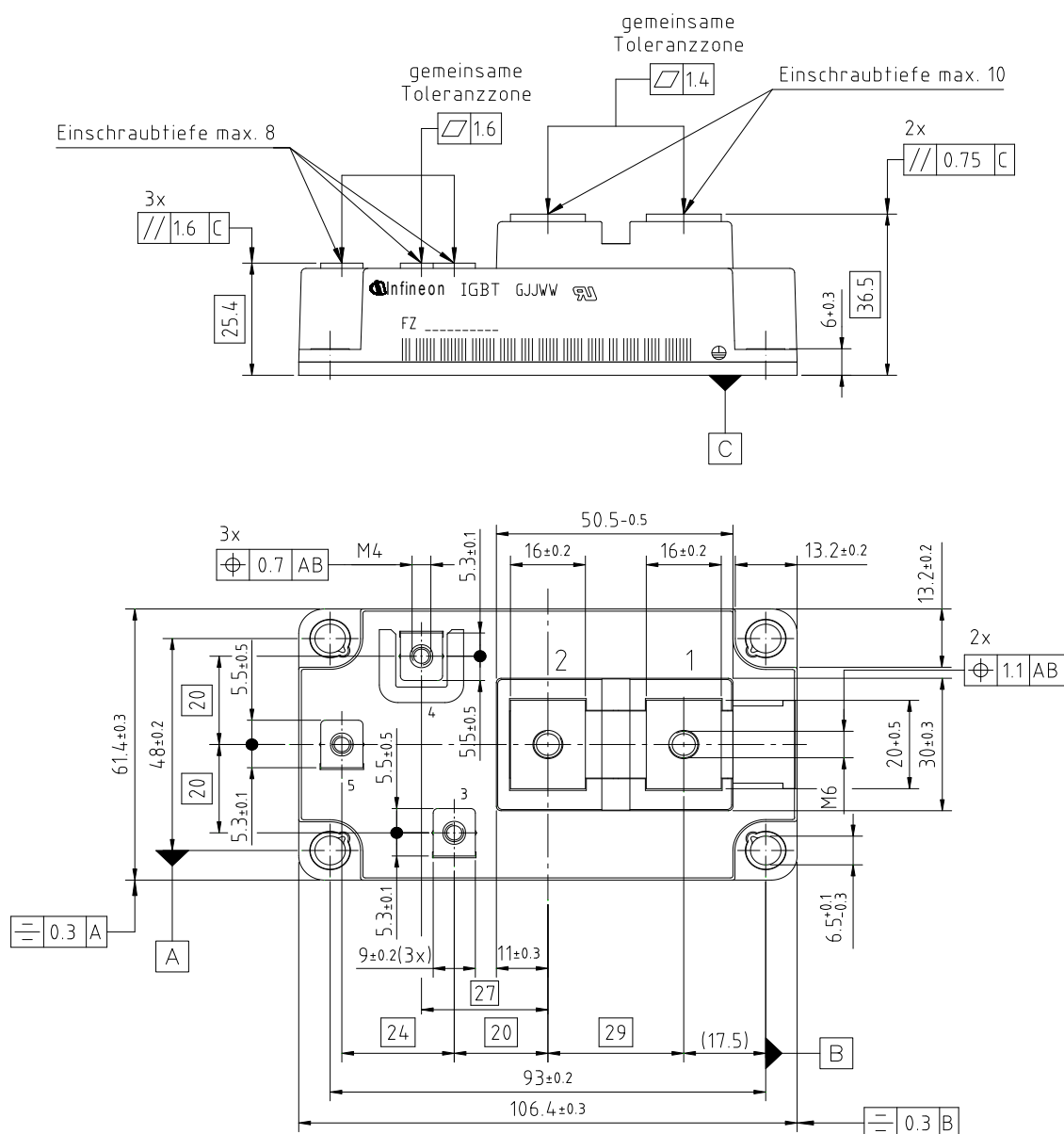
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接线图 / circuit_diagram_headline



封裝尺寸 / package outlines



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使用条件和条款

使用条件和条款

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- the conclusion of Quality Agreements;

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Электрон
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